

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of :  
Beom-jun JIN et al. : Attn: Applications Branch  
Serial No. (New) : Attorney Docket No. SEC.872D  
Filed: October 16, 2003 :  
For: SEMICONDUCTOR MEMORY DEVICE HAVING MULTI-LAYERED STORAGE  
NODE CONTACT PLUG AND METHOD FOR FABRICATING THE SAME

INFORMATION DISCLOSURE STATEMENT  
(SUBMISSION WITH CONTINUATION-IN-PART OR  
RULE 1.53(b) CONTINUATION OR DIVISIONAL APPLICATION)

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. §§ 1.97 and 1.98, applicant(s) hereby submit(s) an Information Disclosure Statement for consideration by the Examiner.

I. LIST OF PATENTS, PUBLICATIONS OR OTHER INFORMATION

The patents, publications or other information submitted for consideration by the Office are listed on PTO-1449 form(s), attached hereto.

II. REFERENCES PREVIOUSLY CITED OR SUBMITTED

Pursuant to 37 C.F.R. § 1.98(d), consideration of information listed on the PTO-1449 form(s) is requested since any patents, publications or other information which are listed on the PTO-1449 form(s) but for which copies are not enclosed herewith, were previously cited by or submitted to the PTO in one of the following applications which has been relied upon for an earlier filing date under 35 U.S.C. § 120:

U.S. Serial Number

10/012,563

U.S. Filing Date

December 12, 2001

III. FEES

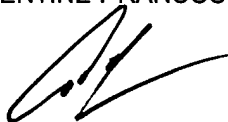
This Information Disclosure Statement is being filed concurrent with the filing of a continuation-in-part, continuation or divisional patent application; therefore, no fee is required.

If the Examiner has any questions concerning this IDS or requires a copy of any of the references cited but not provided, he/she is requested to contact the undersigned. If it is determined that this IDS has been filed under the wrong rule, the PTO is requested to consider this IDS under the proper rule (with a petition if necessary) and charge the appropriate fee to Deposit Account No. 50-0238.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 50-0238 for any additional fee required under 37 C.F.R. §§ 1.16 or 1.17; particularly, extension of time fees.

Respectfully submitted,

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Dated: October 16, 2003

# INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Applicant(s)

Filing Date

Group Art Unit

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A	6,137,130	10/2000	SUNG			
	B	6,136,646	10/2000	LINLIU et al.			
	C	US 2002/0037644A1	03/2002	RHA et al.			
	D	6,180,970 B1	01/2001	HWANG et al.			
	E	6,239,461 B1	05/2001	LEE			
	F	5,296,095	03/1994	NABESHIMA et al.			
	G	5,726,499	03/1998	IRINODA			
	H	6,348,709 B1	02/2002	GRAETTINGER et al.			

## FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
	I	5-13750	01/22/1993	JAPAN				
	J	7-297280	11/10/1995	JAPAN				
	K	JP407297280A	10/1995	JAPAN				
	L	JP2000-040805A	02/2000	JAPAN				
	M	2001-0055403	07/04/2001	REPUBLIC OF KOREA				

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	N	Miyashita, T. et al., "A Novel Bit-Line Process using Ploy-Si Masked Dual-Damascene (PMDD) for 0.13 microm DRAMs and Beyond", in Electron Devices Mtg, 2000, IEDM Techn. Digest, 12/10/2000-12/13/2000, San Francisco, CA (USA) (INSPEC Accession No: 6880863).

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.